# HCS32MS

## Radiation Hardened Quad 2-Input OR Gate

September 1995

### Features

- 3 Micron Radiation Hardened SOS CMOS
- Total Dose 200K RAD (Si)
- SEP Effective LET No Upsets: >100 MEV-cm$^2$/mg
- Single Event Upset (SEU) Immunity < 2 x $10^{-9}$ Errors/Bit-Day (Typ)
- Dose Rate Survivability: >1 x $10^{12}$ RAD (Si)/s
- Dose Rate Upset >$10^{10}$ RAD (Si)/s 20ns Pulse
- Latch-Up Free Under Any Conditions
- Military Temperature Range: -55$^o$C to +125$^o$C
- Significant Power Reduction Compared to LSTTL ICs
- DC Operating Voltage Range: 4.5V to 5.5V
- Input Logic Levels
  - VIL = 30% of VCC Max
  - VIH = 70% of VCC Min
- Input Current Levels Ii ≤ 5μA @ VOL, VOH

### Description

The Intersil HCS32MS is a Radiation Hardened Quad 2-Input OR Gate. A low on both inputs forces the output to a high state.

The HCS32MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of radiation hardened, high-speed, CMOS/SOS Logic Family.

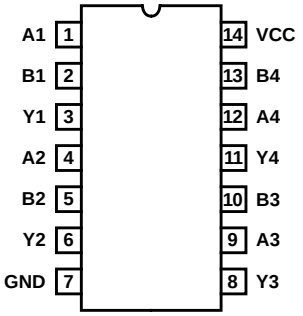
The HCS32MS is supplied in a 14 lead Ceramic flatpack (K suffix) or a SBDIP Package (D suffix).

### Ordering Information

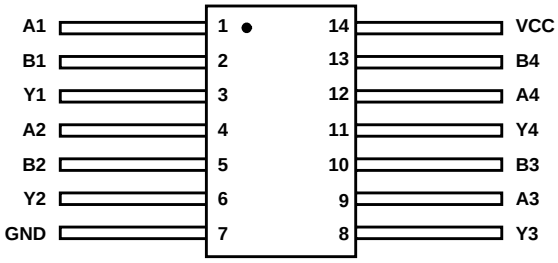
| PART NUMBER | TEMPERATURE RANGE | SCREENING LEVEL | PACKAGE |
|---|---|---|---|
| HCS32DMSR | -55$^o$C to +125$^o$C | Intersil Class S Equivalent | 14 Lead SBDIP |
| HCS32KMSR | -55$^o$C to +125$^o$C | Intersil Class S Equivalent | 14 Lead Ceramic Flatpack |
| HCS32D/ Sample | +25$^o$C | Sample | 14 Lead SBDIP |
| HCS32K/ Sample | +25$^o$C | Sample | 14 Lead Ceramic Flatpack |
| HCS32HMSR | +25$^o$C | Die | Die |

### Pinouts

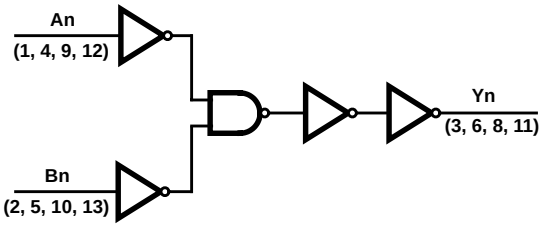
**14 LEAD CERAMIC DUAL-IN-LINE METAL SEAL PACKAGE (SBDIP) MIL-STD-1835 CDIP2-T14**
TOP VIEW




**14 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE (FLATPACK) MIL-STD-1835 CDFP3-F14**
TOP VIEW




### Functional Diagram




**TRUTH TABLE**

| INPUTS | | OUTPUTS |
|---|---|---|
| An | Bn | Yn |
| L | L | L |
| L | H | H |
| H | L | H |
| H | H | H |

NOTE: L = Logic Level Low, H = Logic level High

CAUTION: These devices are sensitive to electrostatic discharge; follow proper IC Handling Procedures.





Spec Number **518768**
File Number **3057.1**

## Absolute Maximum Ratings

Supply Voltage (VCC). . . . . +7.0V
Input Voltage Range, All Inputs . . . . . -0.5V to VCC +0.5V
DC Input Current, Any One Input . . . . . ±10mA
DC Drain Current, Any One Output. . . . . ±25mA
(All Voltage Reference to the VSS Terminal)
Storage Temperature Range (TSTG) . . . . . $-65^oC$ to $+150^oC$
Lead Temperature (Soldering 10sec) . . . . . $+265^oC$
Junction Temperature (TJ) . . . . . $+175^oC$
ESD Classification . . . . . Class 1

## Reliability Information

| Thermal Resistance | $\theta_{JA}$ | $\theta_{JC}$ |
|---|---|---|
| SBDIP Package | $74^oC/W$ | $24^oC/W$ |
| Ceramic Flatpack Package | $116^oC/W$ | $30^oC/W$ |

Maximum Package Power Dissipation at $+125^oC$ Ambient
SBDIP Package. . . . . 0.68W
Ceramic Flatpack Package . . . . . 0.43W
If device power exceeds package dissipation capability, provide heat sinking or derate linearly at the following rate:
SBDIP Package. . . . . $13.5mW/^oC$
Ceramic Flatpack Package . . . . . $8.6mW/^oC$

*CAUTION: As with all semiconductors, stress listed under "Absolute Maximum Ratings" may be applied to devices (one at a time) without resulting in permanent damage. This is a stress rating only. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. The conditions listed under "Electrical Performance Characteristics" are the only conditions recommended for satisfactory device operation..*

## Operating Conditions

Supply Voltage (VCC). . . . . +4.5V to +5.5V
Input Rise and Fall Times at VCC = 4.5V (TR, TF) . . . 100ns/V Max
Operating Temperature Range ($T_A$) . . . . . $-55^oC$ to $+125^oC$
Input Low Voltage (VIL). . . . . 0.0V to 30% of VCC
Input High Voltage (VIH) . . . . . 70% of VCC to VCC

**TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS**

| PARAMETER | SYMBOL | (NOTE 1) CONDITIONS | GROUP A SUB-GROUPS | TEMPERATURE | LIMITS MIN | LIMITS MAX | UNITS |
|---|---|---|---|---|---|---|---|
| Quiescent Current | ICC | VCC = 5.5V, VIN = VCC or GND | 1 | $+25^oC$ | - | 10 | µA |
| | | | 2, 3 | $+125^oC$, $-55^oC$ | - | 200 | µA |
| Output Current (Sink) | IOL | VCC = 4.5V, VIH = 4.5V, VOUT = 0.4V, VIL = 0V | 1 | $+25^oC$ | 4.8 | - | mA |
| | | | 2, 3 | $+125^oC$, $-55^oC$ | 4.0 | - | mA |
| Output Current (Source) | IOH | VCC = 4.5V, VIH = 4.5V, VOUT = VCC -0.4V, VIL = 0V | 1 | $+25^oC$ | -4.8 | - | mA |
| | | | 2, 3 | $+125^oC$, $-55^oC$ | -4.0 | - | mA |
| Output Voltage Low | VOL | VCC = 4.5V, VIH = 3.15V, IOL = 50µA, VIL = 1.35V | 1, 2, 3 | $+25^oC$, $+125^oC$, $-55^oC$ | - | 0.1 | V |
| | | VCC = 5.5V, VIH = 3.85V, IOL = 50µA, VIL = 1.65V | 1, 2, 3 | $+25^oC$, $+125^oC$, $-55^oC$ | - | 0.1 | V |
| Output Voltage High | VOH | VCC = 4.5V, VIH = 3.15V, IOH = -50µA, VIL = 1.35V | 1, 2, 3 | $+25^oC$, $+125^oC$, $-55^oC$ | VCC -0.1 | - | V |
| | | VCC = 5.5V, VIH = 3.85V, IOH = -50µA, VIL = 1.65V | 1, 2, 3 | $+25^oC$, $+125^oC$, $-55^oC$ | VCC -0.1 | - | V |
| Input Leakage Current | IIN | VCC = 5.5V, VIN = VCC or GND | 1 | $+25^oC$ | - | ±0.5 | µA |
| | | | 2, 3 | $+125^oC$, $-55^oC$ | - | ±5.0 | µA |
| Noise Immunity Functional Test | FN | VCC = 4.5V, VIH = 0.70(VCC), VIL = 0.30(VCC), (Note 2) | 7, 8A, 8B | $+25^oC$, $+125^oC$, $-55^oC$ | - | - | - |

NOTES:

1. All voltages reference to device GND.
2. For functional tests VO ≥ 4.0V is recognized as a logic "1", and VO ≤ 0.5V is recognized as a logic "0".

**TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS**

| PARAMETER | SYMBOL | (NOTES 1, 2) CONDITIONS | GROUP A SUB-GROUPS | TEMPERATURE | LIMITS | | UNITS |
|---|---|---|---|---|---|---|---|
| | | | | | MIN | MAX | |
| Input to Output | TPHL | VCC = 4.5V | 9 | +25°C | 2 | 18 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 20 | ns |
| Data to Output | TPLH | VCC = 4.5V | 9 | +25°C | 2 | 20 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 22 | ns |

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume RL = 500Ω, CL = 50pF, Input tr = tf = 3ns, VIL = GND, VIH = VCC.

**TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS**

| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | LIMITS | | UNITS |
|---|---|---|---|---|---|---|---|
| | | | | | MIN | MAX | |
| Capacitance Power Dissipation | CPD | VCC = 5.0V, f = 1MHz | 1 | +25°C | - | 6 | pF |
| | | | 1 | +125°C, -55°C | - | 11 | pF |
| Input Capacitance | CIN | VCC = 5.0V, f = 1MHz | 1 | +25°C | - | 10 | pF |
| | | | 1 | +125°C | - | 10 | pF |
| Output Transition Time | TTHL TTLH | VCC = 4.5V | 1 | +25°C | - | 15 | ns |
| | | | 1 | +125°C | - | 22 | ns |

NOTE:

1. The parameters listed in Table 3 are controlled via design or process parameters. Min and Max Limits are guaranteed but not directly tested. These parameters are characterized upon initial design release and upon design changes which affect these characteristics.

**TABLE 4. DC POST RADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS**

| PARAMETER | SYMBOL | (NOTES 1, 2) CONDITIONS | TEMPERATURE | 200K RAD LIMITS | | UNITS |
|---|---|---|---|---|---|---|
| | | | | MIN | MAX | |
| Quiescent Current | ICC | VCC = 5.5V, VIN = VCC or GND | +25°C | - | 0.2 | mA |
| Output Current (Sink) | IOL | VCC = 4.5V, VIN = VCC or GND, VOUT = 0.4V | +25°C | 4.0 | - | mA |
| Output Current (Source) | IOH | VCC = 4.5V, VIN = VCC or GND, VOUT = VCC -0.4V | +25°C | -4.0 | - | mA |
| Output Voltage Low | VOL | VCC = 4.5V and 5.5V, VIH = 0.70(VCC), VIL = 0.30(VCC), IOL = 50µA | +25°C | - | 0.1 | V |
| Output Voltage High | VOH | VCC = 4.5V and 5.5V, VIH = 0.70(VCC), VIL = 0.30(VCC), IOH = -50µA | +25°C | VCC -0.1 | - | V |

**TABLE 4. DC POST RADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)**

| PARAMETER | SYMBOL | (NOTES 1, 2) CONDITIONS | TEMPERATURE | 200K RAD LIMITS | | UNITS |
|---|---|---|---|---|---|---|
| | | | | MIN | MAX | |
| Input Leakage Current | IIN | VCC = 5.5V, VIN = VCC or GND | +25°C | - | ±5 | µA |
| Noise Immunity Functional Test | FN | VCC = 4.5V, VIH = 0.70(VCC), VIL = 0.30(VCC), (Note 3) | +25°C | - | - | - |
| Data to Output | TPHL | VCC = 4.5V | +25°C | 2 | 20 | ns |
| | TPLH | VCC = 4.5V | +25°C | 2 | 22 | ns |

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume RL = 500Ω, CL = 50pF, Input TR = TF = 3ns, VIL = GND, VIH = VCC.
3. For functional tests VO ≥ 4.0V is recognized as a logic “1”, and VO ≤ 0.5V is recognized as a logic “0”.

**TABLE 5. BURN-IN AND OPERATING LIFE TEST, DELTA PARAMETERS (+25°C)**

| PARAMETER | GROUP B SUBGROUP | DELTA LIMIT |
|---|---|---|
| ICC | 5 | 3µA |
| IOL/IOH | 5 | -15% of 0 Hour |

**TABLE 6. APPLICABLE SUBGROUPS**

| CONFORMANCE GROUPS | | METHOD | GROUP A SUBGROUPS | READ AND RECORD |
|---|---|---|---|---|
| Initial Test (Preburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| Interim Test I (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| Interim Test II (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| PDA | | 100%/5004 | 1, 7, 9, Deltas | |
| Interim Test III (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| PDA | | 100%/5004 | 1, 7, 9, Deltas | |
| Final Test | | 100%/5004 | 2, 3, 8A, 8B, 10, 11 | |
| Group A (Note 1) | | Sample/5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11 | |
| Group B | Subgroup B-5 | Sample/5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas | Subgroups 1, 2, 3, 9, 10, 11, (Note 2) |
| | Subgroup B-6 | Sample/5005 | 1, 7, 9 | |
| Group D | | Sample/5005 | 1, 7, 9 | |

NOTES:

1. Alternate group A inspection in accordance with method 5005 of MIL-STD-883 may be exercised.
2. Table 5 parameters only.

**TABLE 7. TOTAL DOSE IRRADIATION**

| CONFORMANCE GROUPS | METHOD | TEST | | READ AND RECORD | |
|---|---|---|---|---|---|
| | | PRE RAD | POST RAD | PRE RAD | POST RAD |
| Group E Subgroup 2 | 5005 | 1, 7, 9 | Table 4 | 1, 9 | Table 4 (Note 1) |

NOTE:

1. Except FN test which will be performed 100% Go/No-Go.

**TABLE 8. STATIC AND DYNAMIC BURN-IN TEST CONNECTIONS**

| OPEN | GROUND | 1/2 VCC = 3V ± 0.5V | VCC = 6V ± 0.5V | OSCILLATOR | |
|---|---|---|---|---|---|
| | | | | 50kHz | 25kHz |
| STATIC BURN-IN I TEST CONNECTIONS (Note 1) | | | | | |
| 3, 6, 8, 11 | 1, 2, 4, 5, 7, 9, 10, 12, 13 | - | 14 | - | - |
| STATIC BURN-IN II TEST CONNECTIONS (Note 1) | | | | | |
| 3, 6, 8, 11 | 7 | - | 1, 2, 4, 5, 9, 10, 12, 13, 14 | - | - |
| DYNAMIC BURN-IN TEST CONNECTIONS (Note 2) | | | | | |
| - | 7 | 3, 6, 8, 11 | 14 | 1, 2, 4, 5, 9, 10, 12, 13 | - |

NOTES:

1. Each pin except VCC and GND will have a resistor of 10kΩ ± 5% for static burn-in
2. Each pin except VCC and GND will have a resistor of 1kΩ ± 5% for dynamic burn-in

**TABLE 9. IRRADIATION TEST CONNECTIONS**

| OPEN | GROUND | VCC = 5V ± 0.5V |
|---|---|---|
| 3, 6, 8, 11 | 7 | 1, 2, 4, 5, 9, 10, 12, 13, 14 |

NOTE: Each pin except VCC and GND will have a resistor of 47KΩ ± 5% for irradiation testing. Group E, Subgroup 2, sample size is 4 dice/wafer 0 failures.

## Intersil Space Level Product Flow - 'MS'

Wafer Lot Acceptance (All Lots) Method 5007 (Includes SEM)

GAMMA Radiation Verification (Each Wafer) Method 1019, 4 Samples/Wafer, 0 Rejects

100% Nondestructive Bond Pull, Method 2023

Sample - Wire Bond Pull Monitor, Method 2011

Sample - Die Shear Monitor, Method 2019 or 2027

100% Internal Visual Inspection, Method 2010, Condition A

100% Temperature Cycle, Method 1010, Condition C, 10 Cycles

100% Constant Acceleration, Method 2001, Condition per Method 5004

100% PIND, Method 2020, Condition A

100% External Visual

100% Serialization

100% Initial Electrical Test (T0)

100% Static Burn-In 1, Condition A or B, 24 hrs. min., +125$^{o}$C min., Method 1015

100% Interim Electrical Test 1 (T1)

100% Delta Calculation (T0-T1)

100% Static Burn-In 2, Condition A or B, 24 hrs. min., +125$^{o}$C min., Method 1015

100% Interim Electrical Test 2 (T2)

100% Delta Calculation (T0-T2)

100% PDA 1, Method 5004 (Notes 1and 2)

100% Dynamic Burn-In, Condition D, 240 hrs., +125$^{o}$C or Equivalent, Method 1015

100% Interim Electrical Test 3 (T3)

100% Delta Calculation (T0-T3)

100% PDA 2, Method 5004 (Note 2)

100% Final Electrical Test

100% Fine/Gross Leak, Method 1014

100% Radiographic, Method 2012 (Note 3)

100% External Visual, Method 2009

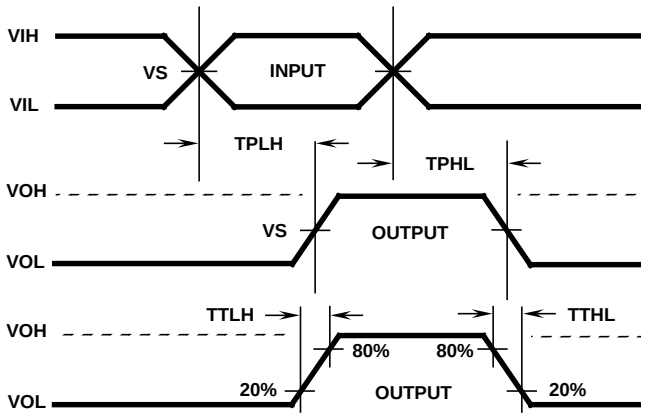
Sample - Group A, Method 5005 (Note 4)

100% Data Package Generation (Note 5)

NOTES:

1. Failures from Interim electrical test 1 and 2 are combined for determining PDA 1.
2. Failures from subgroup 1, 7, 9 and deltas are used for calculating PDA. The maximum allowable PDA = 5% with no more than 3% of the failures from subgroup 7.
3. Radiographic (X-Ray) inspection may be performed at any point after serialization as allowed by Method 5004.
4. Alternate Group A testing may be performed as allowed by MIL-STD-883, Method 5005.
5. Data Package Contents:
   - Cover Sheet (Intersil Name and/or Logo, P.O. Number, Customer Part Number, Lot Date Code, Intersil Part Number, Lot Number, Quantity).
   - Wafer Lot Acceptance Report (Method 5007). Includes reproductions of SEM photos with percent of step coverage.
   - GAMMA Radiation Report. Contains Cover page, disposition, Rad Dose, Lot Number, Test Package used, Specification Numbers, Test equipment, etc. Radiation Read and Record data on file at Intersil.
   - X-Ray report and film. Includes penetrometer measurements.
   - Screening, Electrical, and Group A attributes (Screening attributes begin after package seal).
   - Lot Serial Number Sheet (Good units serial number and lot number).
   - Variables Data (All Delta operations). Data is identified by serial number. Data header includes lot number and date of test.
   - The Certificate of Conformance is a part of the shipping invoice and is not part of the Data Book. The Certificate of Conformance is signed by an authorized Quality Representative.

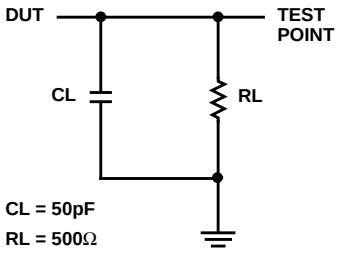
## AC Timing Diagrams




**AC VOLTAGE LEVELS**

| PARAMETER | HCS | UNITS |
|---|---|---|
| VCC | 4.50 | V |
| VIH | 4.50 | V |
| VS | 2.25 | V |
| VIL | 0 | V |
| GND | 0 | V |

## AC Load Circuit



## Die Characteristics

**DIE DIMENSIONS:**

87 x 88 mils
2.20 x 2.2mm

**METALLIZATION:**

Type: SiAl
Metal Thickness: 11kÅ ± 1kÅ

**GLASSIVATION:**

Type: $SiO_2$
Thickness: 13kÅ ± 2.6kÅ

**WORST CASE CURRENT DENSITY:**

$<2.0 \times 10^5 A/cm^2$

**BOND PAD SIZE:**

100µm x 100µm
4 x 4 mils

## Metallization Mask Layout

**HCS32MS**